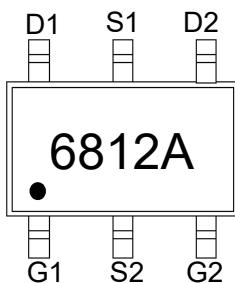


## Features

- Excellent package for good heat dissipation
- Ultra low gate charge
- Low reverse transfer capacitance
- Fast switching capability
- Avalanche energy specified

## Application

- Power switching application



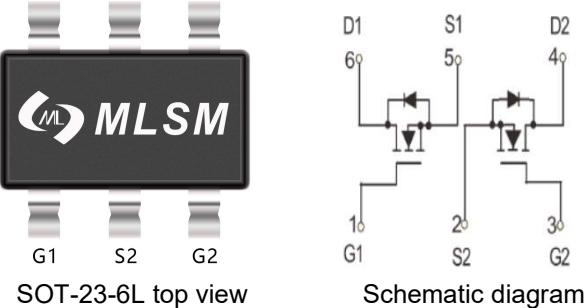
6812A: Device code

## Product Summary

V <sub>DS</sub>	R <sub>DS(ON)</sub> MAX	I <sub>D</sub> MAX
60V	100mΩ@10V	3A
	120mΩ@4.5V	



SOT-23-6L top view



Schematic diagram



Halogen-Free

Marking and pin assignment

## Absolute Maximum Ratings (TA=25°C unless otherwise noted)

Symbol	Parameter	Rating	Unit	
<b>Common Ratings (TC=25°C Unless Otherwise Noted)</b>				
V <sub>DS</sub>	Drain-Source Breakdown Voltage	60	V	
V <sub>GS</sub>	Gate-Source Voltage	±20	V	
T <sub>J</sub>	Maximum Junction Temperature	150	°C	
T <sub>STG</sub>	Storage Temperature Range	-55 to 150	°C	
I <sub>S</sub>	Diode Continuous Forward Current	3	A	
<b>Mounted on Large Heat Sink</b>				
I <sub>DM</sub>	Pulse Drain Current Tested	T <sub>c</sub> =25°C	14	A
I <sub>D</sub>	Continuous Drain Current	T <sub>c</sub> =25°C	3	A
P <sub>D</sub>	Maximum Power Dissipation	T <sub>c</sub> =25°C	1.1	W
R <sub>θJA</sub>	Thermal Resistance Junction-Ambient		114 °C/W	

## Ordering Information (Example)

Type	Package	Marking	Minimum Package(pcs)	Inner Box Quantity(pcs)	Outer Carton Quantity(pcs)	Delivery Mode
MLSL6812A	SOT-23-6L	6812A	3,000	6,000	42,000	13" reel

**Electrical Characteristics (T<sub>J</sub>=25°C unless otherwise noted)**

Symbol	Parameter	Condition	Min	Typ	Max	Unit
<b>Static Electrical Characteristics @ T<sub>J</sub> = 25°C (unless otherwise stated)</b>						
BV <sub>(BR)DSS</sub>	Drain-Source Breakdown Voltage	V <sub>GS</sub> =0V, I <sub>D</sub> =250μA	60	--	--	V
I <sub>DSS</sub>	Zero Gate Voltage Drain Current	V <sub>DS</sub> =60V, V <sub>GS</sub> =0V	--	--	1	μA
I <sub>GSS</sub>	Gate-Body Leakage Current	V <sub>GS</sub> =±20V, V <sub>DS</sub> =0V	--	--	±100	nA
V <sub>GS(th)</sub>	Gate Threshold Voltage	V <sub>DS</sub> =V <sub>GS</sub> , I <sub>D</sub> =250μA	1.0	1.5	2.5	V
R <sub>DS(on)</sub>	Drain-Source On-State Resistance	V <sub>GS</sub> =10V, I <sub>D</sub> =2A	--	62	100	mΩ
		V <sub>GS</sub> =4.5V, I <sub>D</sub> =1A	--	70	120	mΩ

**Dynamic Electrical Characteristics @ T<sub>J</sub> = 25°C (unless otherwise stated)**

C <sub>ISS</sub>	Input Capacitance	V <sub>DS</sub> =30V, V <sub>GS</sub> =0V, f=1MHz	--	400	--	pF
C <sub>OSS</sub>	Output Capacitance		--	28	--	pF
C <sub>RSS</sub>	Reverse Transfer Capacitance		--	23	--	pF

**Switching Characteristics**

Q <sub>g</sub>	Total Gate Charge	V <sub>DS</sub> =30V, I <sub>D</sub> =3A, V <sub>GS</sub> =10V	--	9	--	nC
Q <sub>gs</sub>	Gate Source Charge		--	1	--	nC
Q <sub>gd</sub>	Gate Drain Charge		--	2.5	--	nC
t <sub>d(on)</sub>	Turn-on Delay Time	V <sub>DD</sub> =30V, I <sub>D</sub> =3A, V <sub>GS</sub> =10V, R <sub>G</sub> =2.3Ω	--	4	--	nS
t <sub>r</sub>	Turn-on Rise Time		--	10	--	nS
t <sub>d(off)</sub>	Turn-Off Delay Time		--	12.5	--	nS
t <sub>f</sub>	Turn-Off Fall Time		--	1.8	--	nS

**Source-Drain Diode Characteristics**

V <sub>SD</sub>	Forward on voltage	T <sub>J</sub> =25°C, I <sub>S</sub> =3A	--	0.8	1.2	V
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### Typical Operating Characteristics

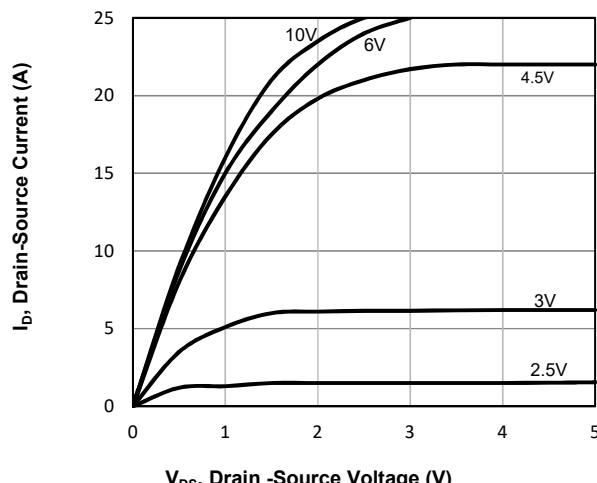


Fig1. Typical Output Characteristics

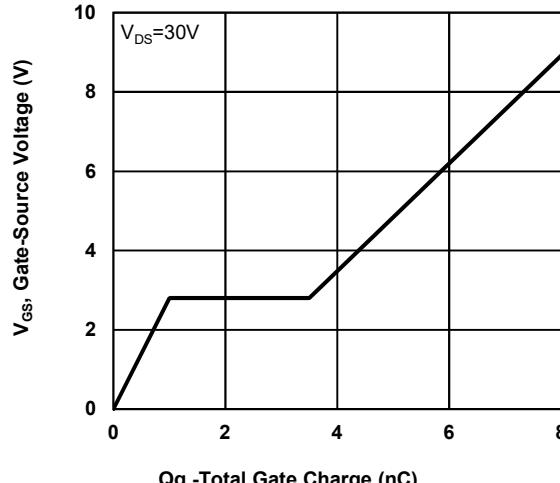


Fig2. Typical Gate Charge Vs.Gate-Source Voltage

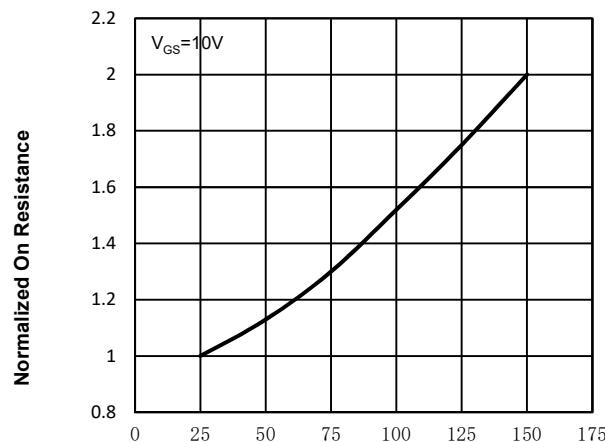


Fig3. Normalized On-Resistance Vs. Temperature

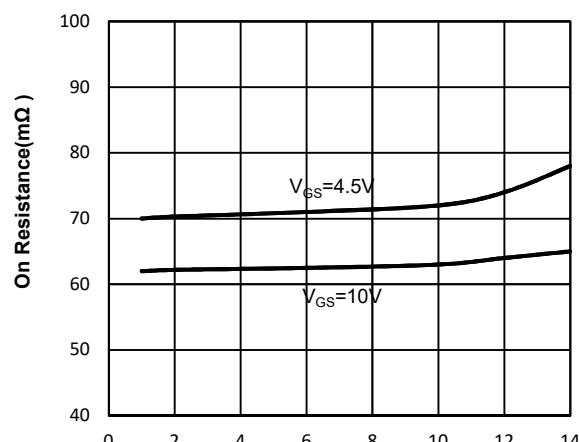


Fig4. On-Resistance Vs. Drain-Source Current

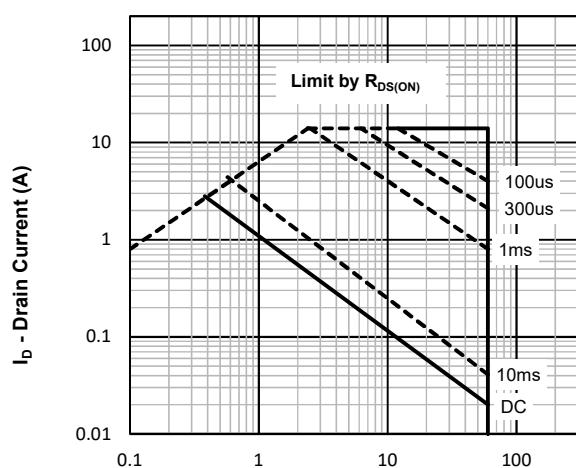


Fig5. Maximum Safe Operating Area

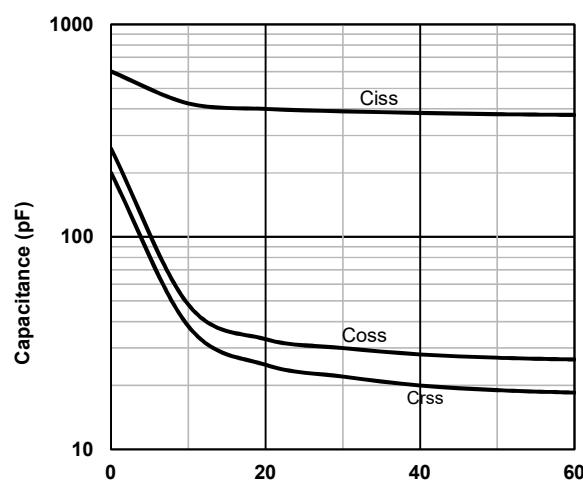
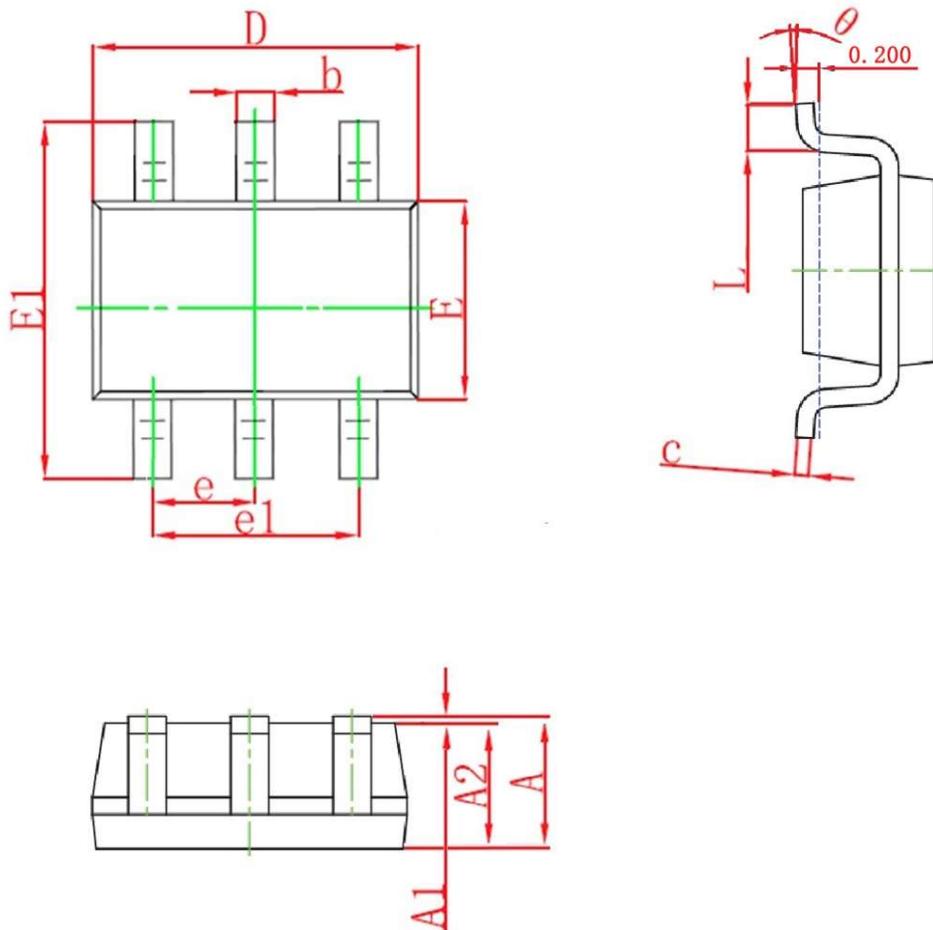


Fig6 Typical Capacitance Vs.Drain-Source Voltage

## SOT-23-6L Package information



Symbol	Dimensions in Millimeters(mm)		Dimensions In Inches	
	Min	Max	Min	Max
A	1.050	1.250	0.041	0.049
A1	0.000	0.100	0.000	0.004
A2	1.000	1.200	0.039	0.047
b	0.300	0.500	0.012	0.020
c	0.100	0.200	0.004	0.008
D	2.820	3.020	0.111	0.119
E	1.500	1.700	0.059	0.067
E1	2.600	3.000	0.102	0.118
e	0.950TYP		0.037TYP	
e1	1.800	2.000	0.071	0.079
L	0.300	0.600	0.012	0.024
K	0°	8°	0°	8°